

## EFFECT OF ANNEALING ON THE Sb<sub>2</sub>S<sub>3</sub> AND CsCL THIN FILMS

**SANJAY KUMAR<sup>\*1</sup>, P. ARUN<sup>2</sup> AND R.P.VATS<sup>3</sup>**

<sup>1</sup>Department of P.G. studies & research in Physics, J.V. Jain College, Saharanpur

<sup>2</sup>Department of physics & electronics, S.G.T.B. Khalsa College, University of Delhi, Delhi.

<sup>3</sup>Department of Physics, M.S. College, Saharanpur,

<sup>\*1</sup>Corresponding author. Tel.:+91-9410608481, 9411484142; Fax: + 0132-2763344

<sup>\*1</sup>E-mail address: skm0088@gmail.com

### ABSTRACT

Crystalline nanoparticles of CsCl were suspended in the amorphous matrix of antimony trisulphide Sb<sub>2</sub>S<sub>3</sub>. Sb<sub>2</sub>S<sub>3</sub> and CsCl has large band gap. The films are deposited on glass substrate by thermal co-evaporation technique at room temperature (300 K). The absorption coefficient  $\alpha$  was determined using the absorbance and transmission measurements from a UV vis double beam spectrometer Shimadzu JAPAN (model UV-2401 PC Shimadzu) at normal incidence of light in the wavelength range 300-900 nm and the structural characterizations were done using XRD(X Ray Diffraction) and morphology study was done by AFM (Atomic Force Microscope) and SEM (Scanning Electron Microscope). Various graphs  $(\alpha h\nu)^{1/2}$  against  $h\nu$  showed that the material has indirect band gap. Thin films have been annealing at different temperature i.e. 100°C and 150°C for one hour in air using by horizontal muffle Furness. After annealing at different temperatures the optical properties of thin films are changed.

**Keywords:** Sb<sub>2</sub>S<sub>3</sub> and CsCl material, Thermal co-evaporation technique, refractive index, extinction coefficient, energy band gap, surface morphology, annealing.

### REFERENCES

- 1 N. Tigau, G. I. Rasu, V. ciupina, G. Prodan, E. Vasile, *J. Optoelectron. Adv. Mater.*, 07, (2005), 727.
- 2 M.T.S. Nair, Y. Pena, J. Compos, V.M. Garcia, P.K. Nair, *J. Electrochem. Soc.*, 145, (1998), 2113.
- 3 S.M. Sze, *Physics of Semiconductor Devices*, Wiley, (New York, 1981).
- 5 I.K. El Zawawi, A. Abdel- Moez, F.S. Terra, M. Mounir, *Thin Solid Films*, 324, (1998), 300.
- 6 A.M. Salem, M. Soliman Selim, *J.Phys. D.Appl. Phys.*, 34, (2001), 12.
- 7 R.S. Mane and C.D. Lokhande, *Mater. Chem. Phys.*, 82, (2003), 347.
- 8 C.D. Lokhande, B.R. Sankpal, R.S. Mane, H.M. Pathan, M.Muller, M.Giersing V.Ganesan, *Appl. Surf.*
- 9 O. Savadogo and K.C. Mandal, *Sol. Ener. Mater. Sol. Cells*, 26, (1992), 117.
- 10 R.S. Mane and C.D. Lokhande, *Mater. Chem. Phys.*, 78,(2003), 385.
- 11 R.S. Mane, B.R. Sankpal and C.D. Lokhande, *Thin Solid Films*, 353, (1999), 29.
- 12 R.S. Mane and C.D. LOkhande, *Surf. Coatings Techn.*, 172 (2003), 51.
- 13 K.Y. Rajpure and C.H. Bhosale, *J. Phys. Chem. Solids*, 61, (2000), 561.
- 14 C.H. Bhosale, M.D. Uplane, P.S. Patil, C.D. Lokhande, *Thin Solid Films*, 2487, (1994), 137.
- 15 K.Y. Ranjpure, A.L. Dhebe, C.D. Lokhande, C.H. Bhosale, *Materials Chemistry and Physics*, 56, (1998), 177.
- 16 B.R. Sankpal, R.S. Mane, C.D. Lokhande, *J.Mater. Sci. Lett.*, 18, (1999), 1453.
- 17 N.S. Yesugade, C.D. Lokhande, C.H. Bhosale, *Thin solid Films*, 263, (1995), 145.

18. R.S. Mane, B.R. Sankapal, C.D. Lokhande, *thin solid Films*, 353, (1999), 29.
19. J.D. Desai, D.D Lokhande, *Thin solid Films*, 237, (1994), 29.
20. N. Tigau, V.Ciupina, G. Prodan, G.I. Rusu, C.Gheorghies, E.Vasile, *J.Optoelectron. Adv. Mater.*, 6, (2004), 211.
21. V.V. Killadar, C.D. Lokhande, C.H. Bhosale, *Mater. Chem. Phys.*, 47, (1997), 104.
22. S.Mahanty, J.M. Merino, M. Leon, *J. Vac. Sci. Technol.*, A15, (1997), 3060.
23. P. Arun, A.G. Vedeshwar, *J.Non-Cryst. Solids*, 220, (1997), 63.
24. D.I. Ezema, *Turk. J.Phys.*, 29, (2005), 105.
25. N.Tigau, V.Ciupina, G.Prodan, G.I. Rusu, C.Gheorghies, E.Vasile, *J.Optolectron, Adv.Matere.*, 5 (2003), 907.
26. R.Swanpole J.Phys. E.Sci. Instrum. Vol.16.11983. Printedin Great Britain.
27. J.Tauc, A.Menth, D.L. Wood Phys. Rev. Lett. 25 (1970), 749.
28. P.Arun Phys. Lett. A.(2007) 157-162.
29. P.Kumar et. Al. Indian J. Pure & Appl. Phys. 44(2006), 690-693.
30. C. Kittel, Introduction to Solid State Physics, 7th ed., John Wiley & Sons Inc., 1996, P.390.
31. Savadogo and K.C. Mondal, sol. Energy Mater. Solar Cells., 26 (1992) 1178.
- 32 .Ghosh & B. P. Verma , Solid State Commun., 31 (1979), 683.
33. S.Kondo, K. Amaya, T. Saito. Materials Science and Engineering B88 (2002) 85-90.
34. A.A. EI-Shazly, M.A.M. Seyam, M.M. EI-Samanoudy, A.H. Ammar, E.M. Assim *Applied Surface Science* 189 (2002) 129-137.